

CLMPTO

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VA

1. A cleaning agent for a semiconductor device containing a hydroxide, water and a compound expressed in the following general formula (I) and/or the following general formula (II):



where EO represents an oxyethylene group, PO represents an oxypropylene group, x and y represent integers satisfying $x/(x + y) = 0.05$ to 0.4 , and z represents a positive integer.



where EO, PO, x, y and z are defined identically to EO, PO, x, y and z in the general formula (I), R represents a residue of alcohol or amine excluding a hydroxyl group or a hydrogen atom of an amino group, and m represents an integer of at least 1.

2. The cleaning agent for a semiconductor device in accordance with claim 1, wherein said hydroxide includes ammonium hydroxide.

3. The cleaning agent for a semiconductor device in accordance with claim 1, wherein said hydroxide is selected from a group consisting of tetramethylammonium hydroxide, a hydroxide of potassium and a hydroxide of sodium.

4. The cleaning agent for a semiconductor device in accordance with claim 1, wherein the concentration of said hydroxide contained in said cleaning agent is 0.01 percent by weight to 31 percent by weight.

5. The cleaning agent for a semiconductor device in accordance with claim 1, wherein the mean molecular weight of the total of said oxypropylene group in said compound expressed in the general formula (I) or (II) is 500 to 5000.

6. The cleaning agent for a semiconductor device in accordance with claim 1, wherein the weight ratio of said compound expressed in the general formula (I) and/or the general formula (II) to said hydroxide is $(0.3 \times 10^{-4} \text{ to } 1):1$.

7. The cleaning agent for a semiconductor device in accordance with claim 1, wherein the pH of said cleaning agent is at least 8.

8. The cleaning agent for a semiconductor device in accordance with claim 1, further containing not more than 1 percent by weight of hydrogen peroxide.

Claims 9-17 are canceled.